

Silicon NPN Power Transistors

BD949

**DESCRIPTION**

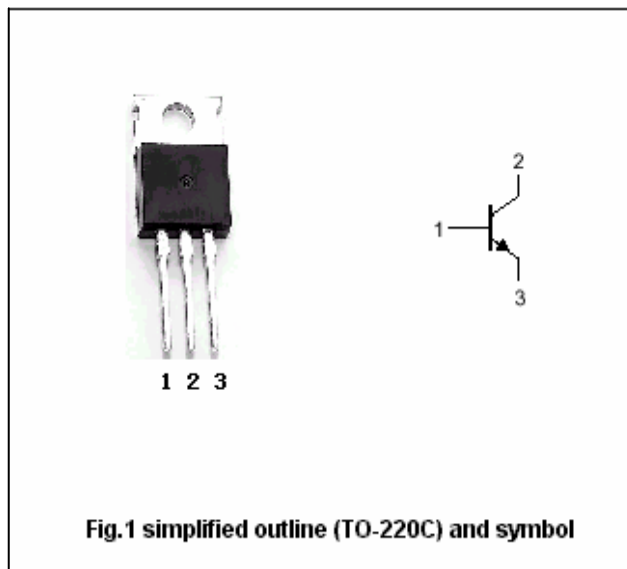
- With TO-220C package
- Low collector saturation voltage
- High current capability

**APPLICATIONS**

- For medium power linear and switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	60	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		5	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	40	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-50~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	60			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.2A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2A; I <sub>B</sub> =0.2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =60V; I <sub>E</sub> =0			50	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			50	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =4V	40			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =2A ; V <sub>CE</sub> =4V	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =4V	3			MHz

